



Science & Technology Facilities Council

Technology

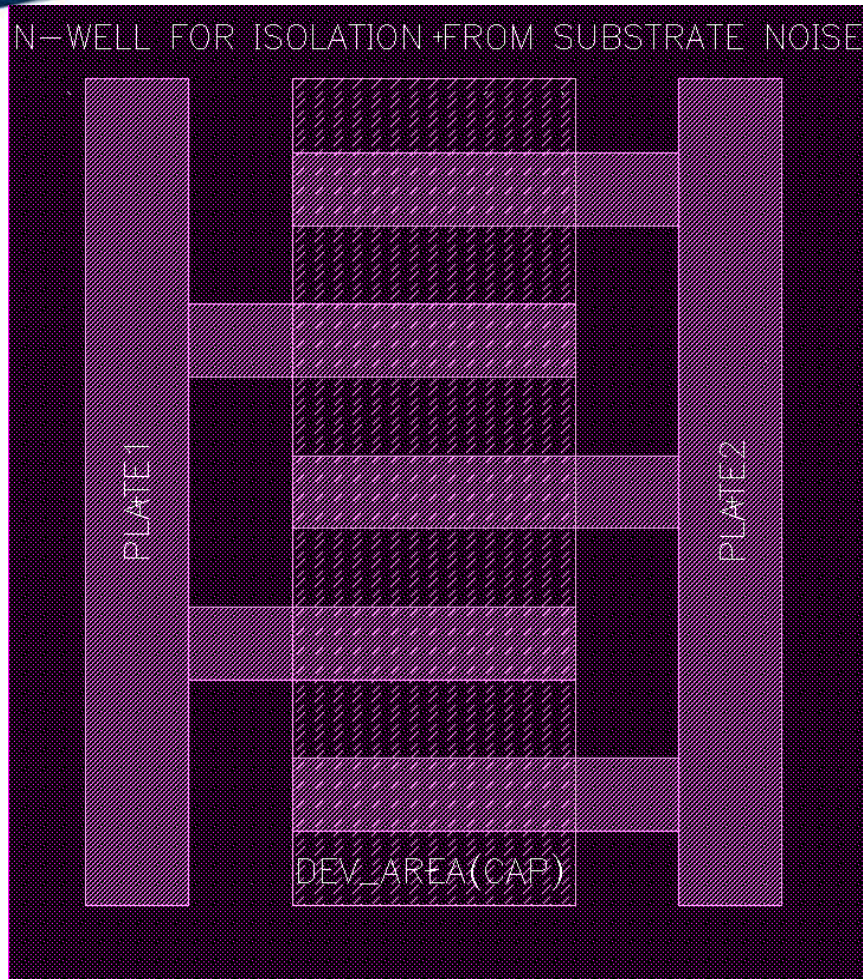
ATLAS Strip CMOS HR-CHESS2
Initial Design Review

Backup Slides

D. Das
STFC-RAL, UK
29/10/15



Pre-amplifier feedback capacitance implementation



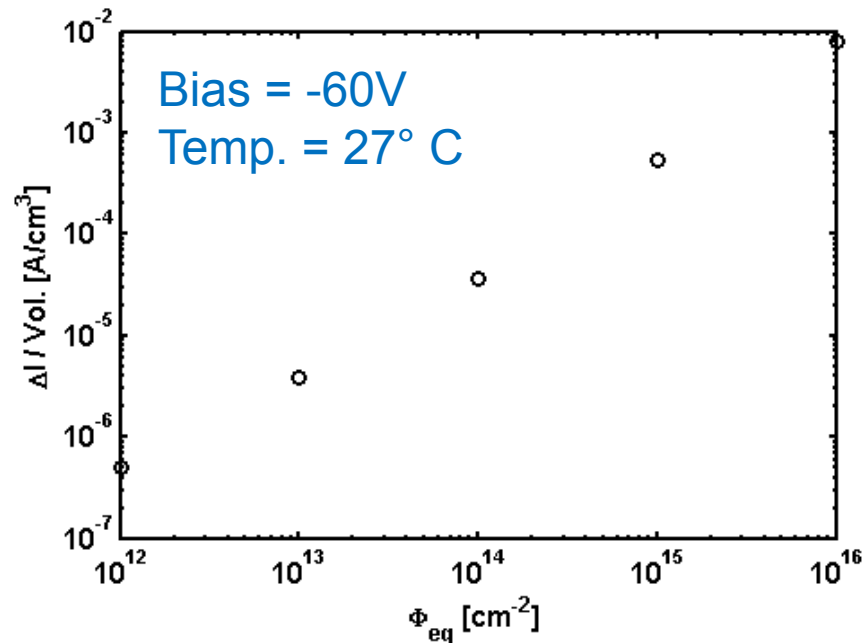
- Used M3, avoided M1 and M2 as they are close to substrate! Didn't stack more metal layers as we want small capacitance $\approx 1\text{fF}$
- TJ allows metal fringe caps not designed according to it's design rules.
- Recognised by LVS, and we can extract it's capacitance using QRC 😊
- Used QRC **field solver**¹ to extract it's cap to be **1.2fF**
- QRC without field solver extracts **0.44fF**, doesn't include fringe capacitance!
- Hand calculations give **0.42fF**, close to QRC w/o field solver!

¹Field solvers provide physically accurate solutions. They calculate electromagnetic parameters by directly solving Maxwell's equations. Due to high calculation burden they are applicable only for very small designs or to parts of the designs.



Leakage current vs geometry from TCAD simulation

During simulated irradiation dark current increases linearly with fluence:



$$\frac{\Delta I}{V} = \alpha \Phi_{eq}$$

V = volume of sensor

ΔI = increase of total leakage current

Φ_{eq} = equivalent fluence

α = Current related damage rate

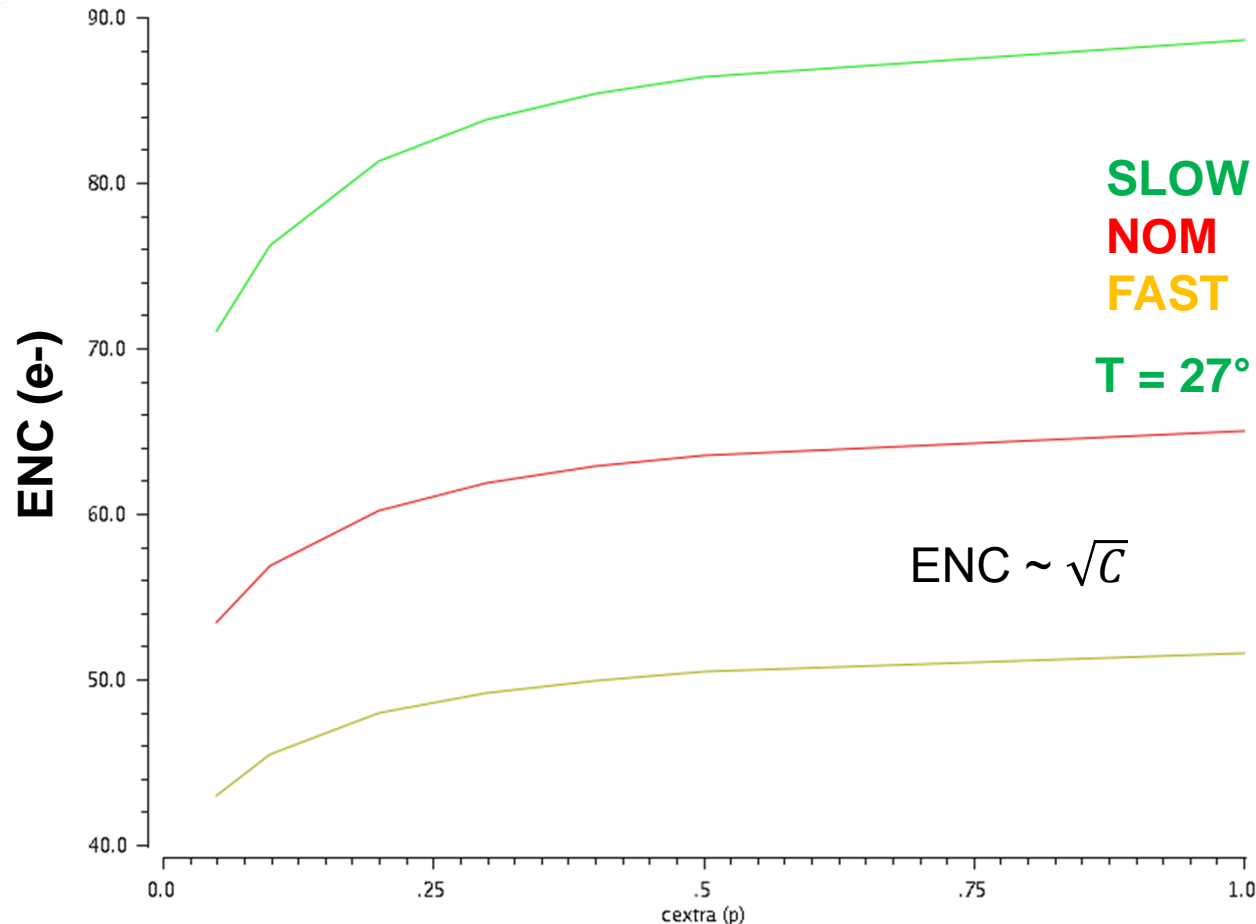
Current related damage rate is temperature dependent $\rightarrow \alpha(T)$

Geometry	Leakage Current @ $1 \times 10^{16} n_{eq} [cm^{-2}]$ Bias = -60V
40μm x 25μm x 40μm	3.2pA
40μm x 25μm x 80μm	6.4pA
40μm x 25μm x 120μm	9.6pA
40μm x 25μm x 200μm	1.6nA
40μm x 25μm x 400μm	3.2nA
40μm x 25μm x 800μm	6.4nA

From simulation results at 27°C:
 $\alpha \approx 80 \times 10^{-18} A/m$



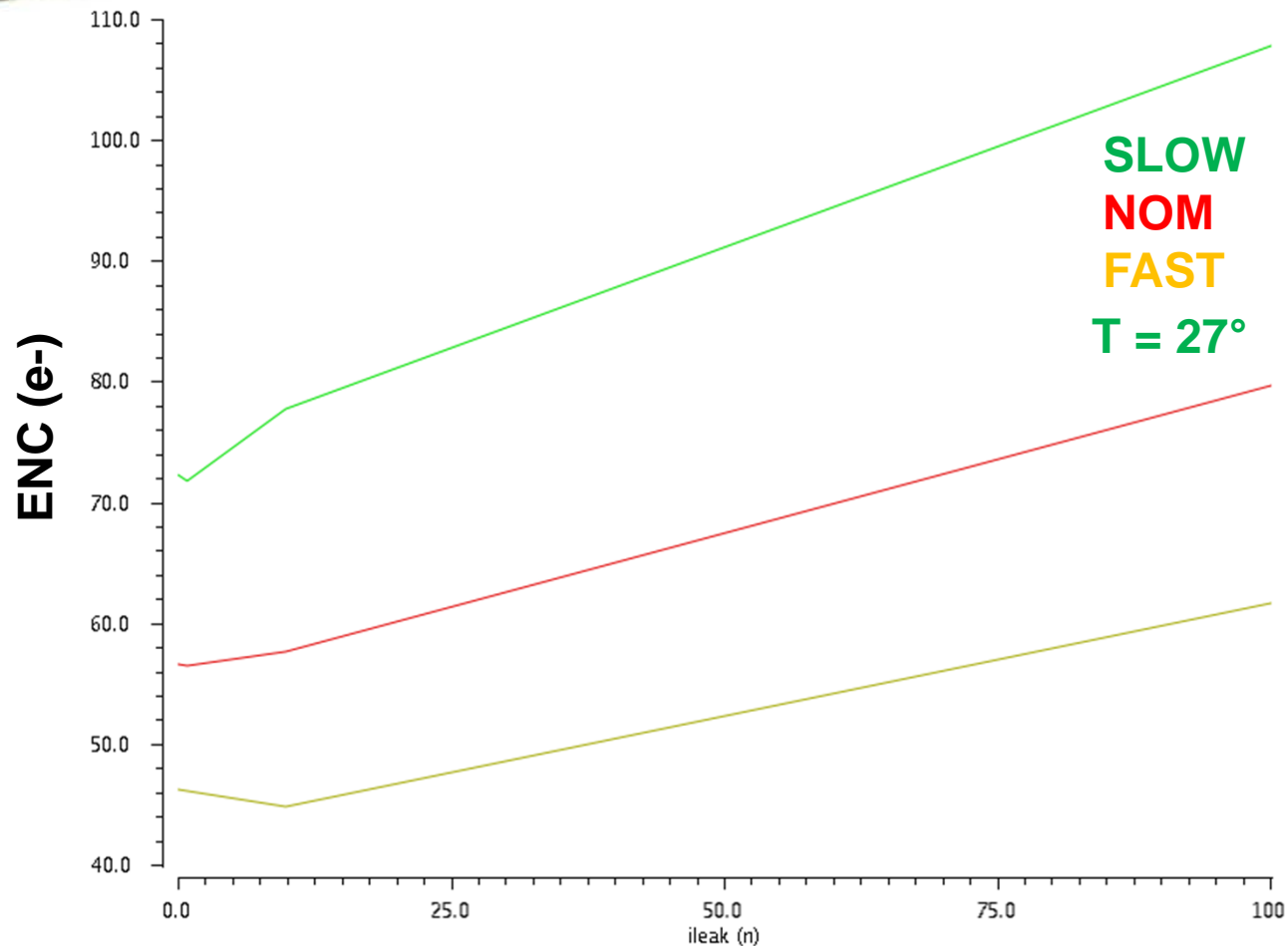
Noise as a function of input capacitance from AC simulation



- Noise at input of comparator as a function of input capacitance
- Process corners: NOM, FAST, SLOW
- I_{leakage} = 0A



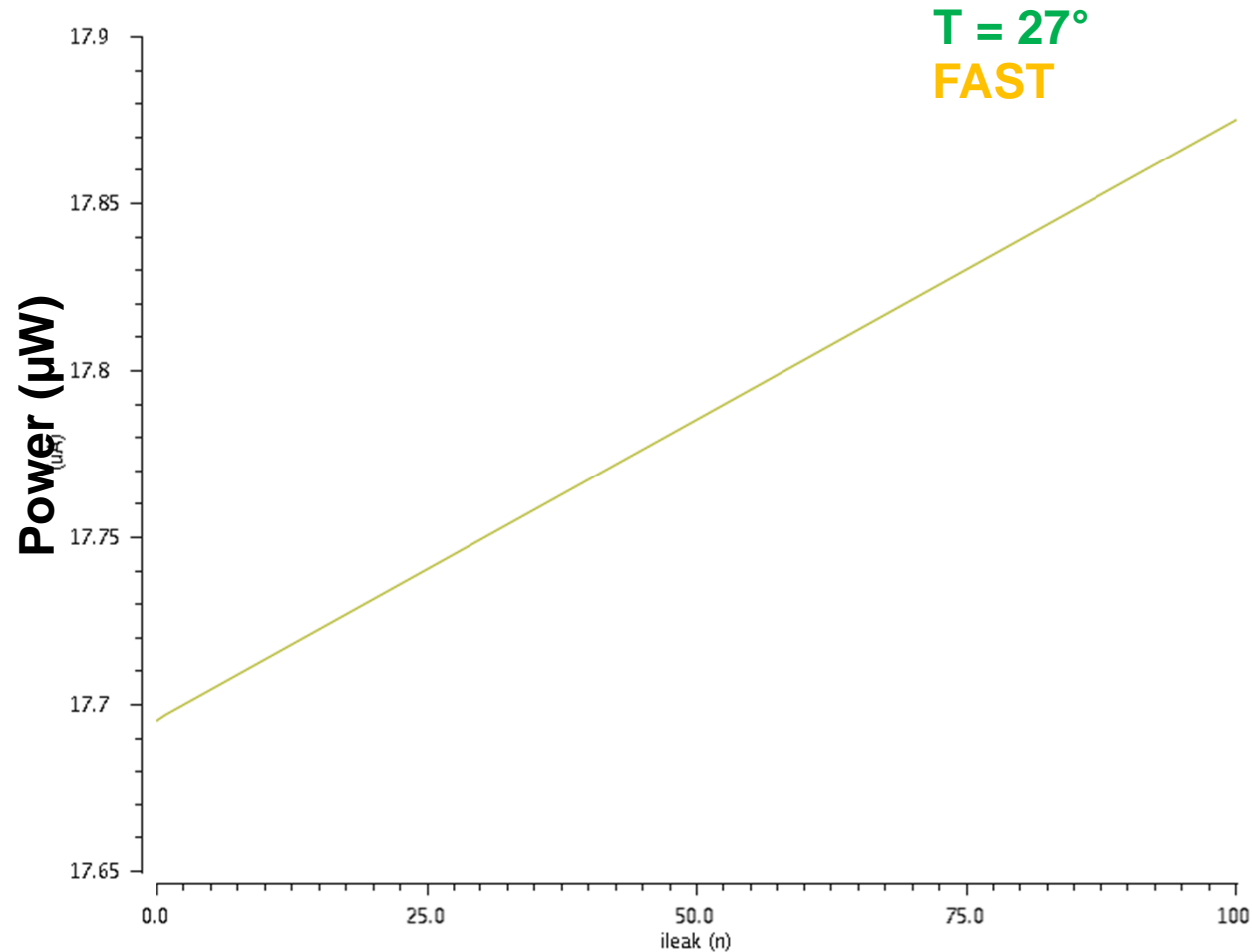
Noise as a function of detector leakage from AC simulation



- Noise at input of comparator as a function of leakage current
- Process corners: NOM, FAST, SLOW



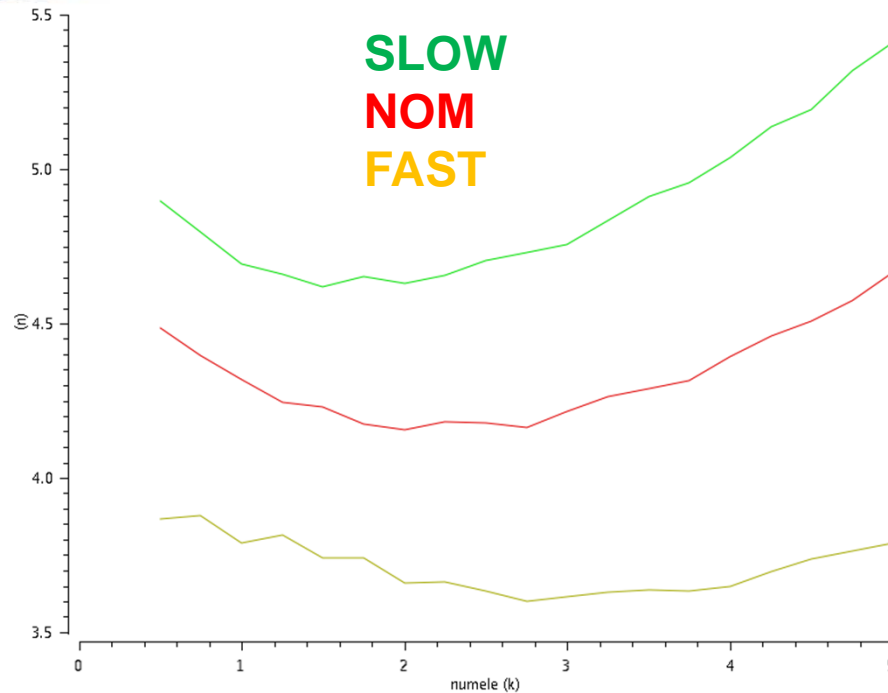
Noise as a function of detector leakage from AC simulation



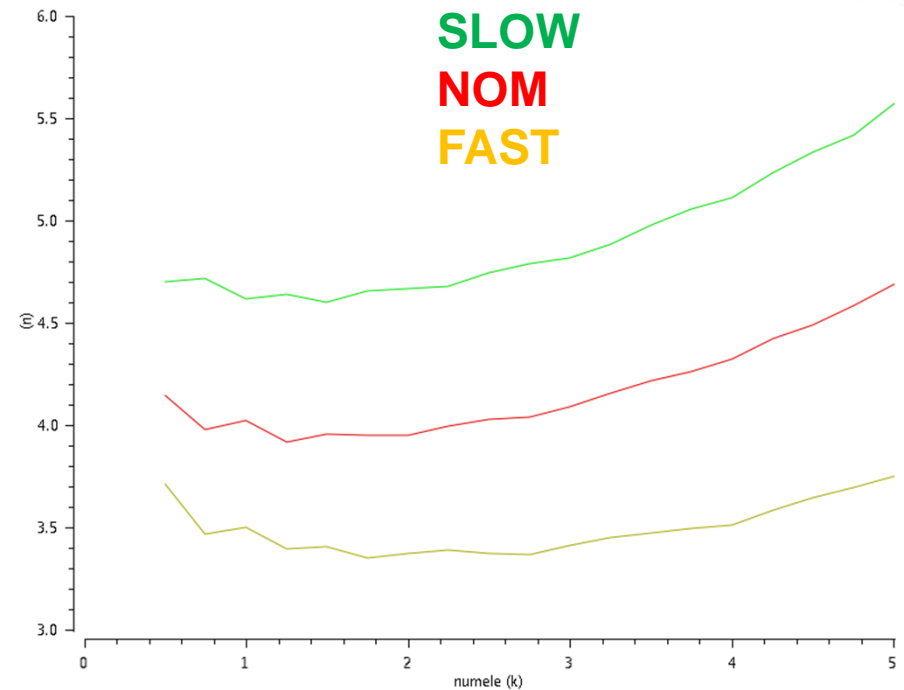
- Power consumption of pre-amplifier as a function of leakage current
- Process corner: FAST (worst case)



Trise at comparator input vs signal



T = +40°

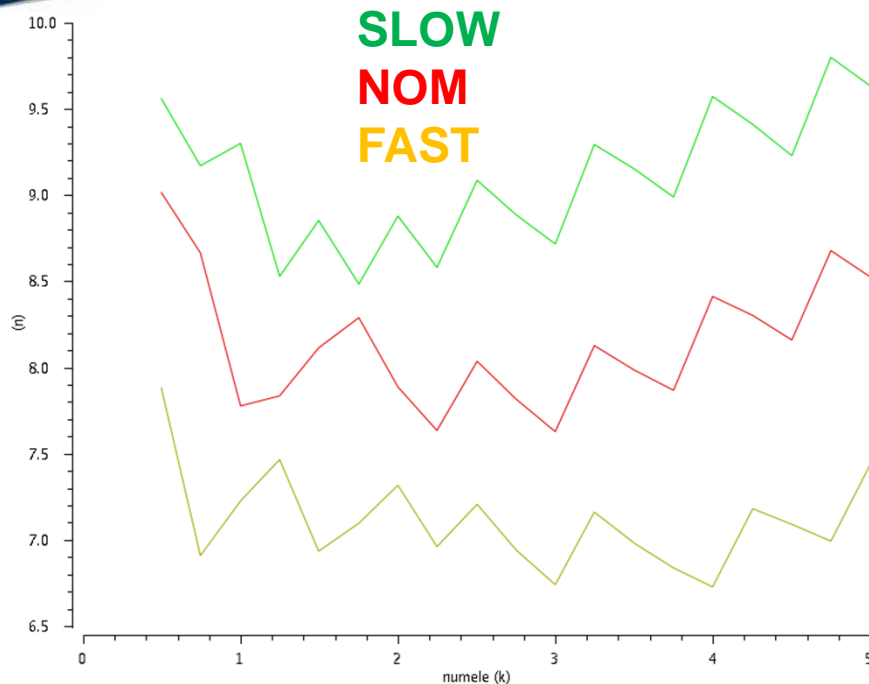


T = -40°

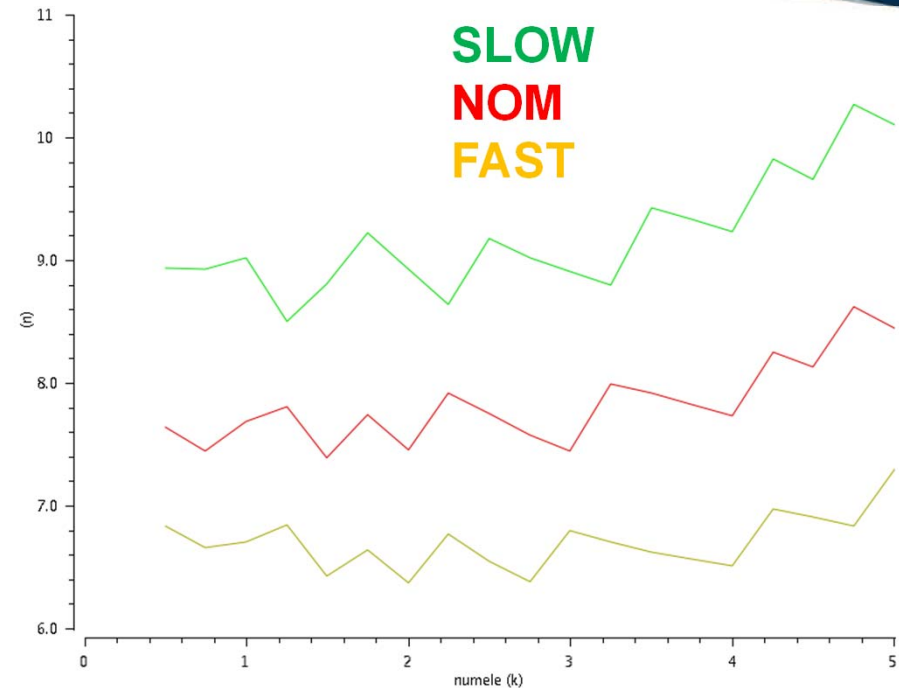
- Trise at input of comparator for signal values from 500e- to 5Ke- in 250e- steps
- Process corners: NOM, FAST, SLOW
- Ileakage = 0A



Tpeaking at comparator input vs signal



T = +40°

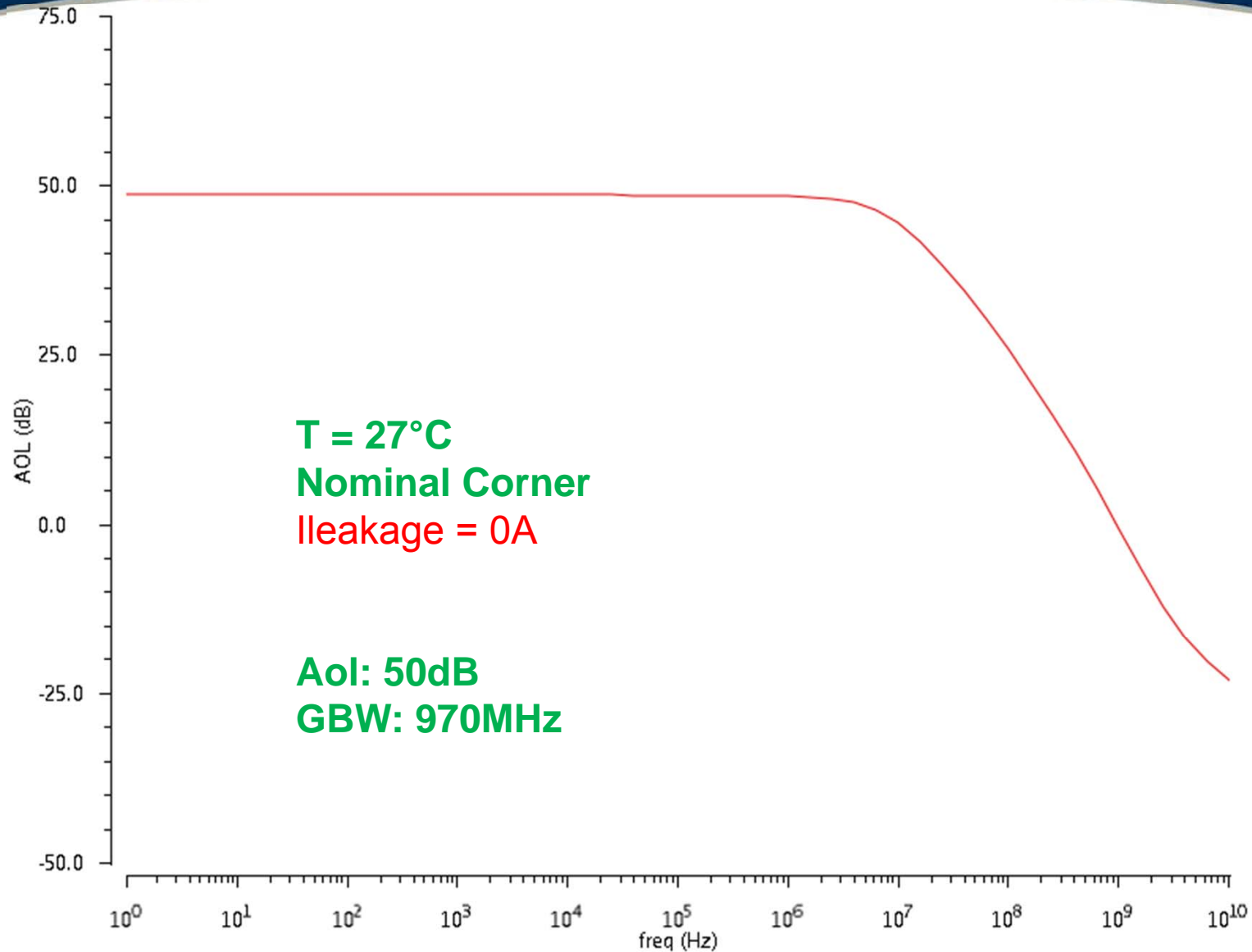


T = -40°

- Tpeaking at input of comparator for signal values from 500e- to 5Ke- in 250e- steps
- Process corners: NOM, FAST, SLOW
- Ileakage = 0A

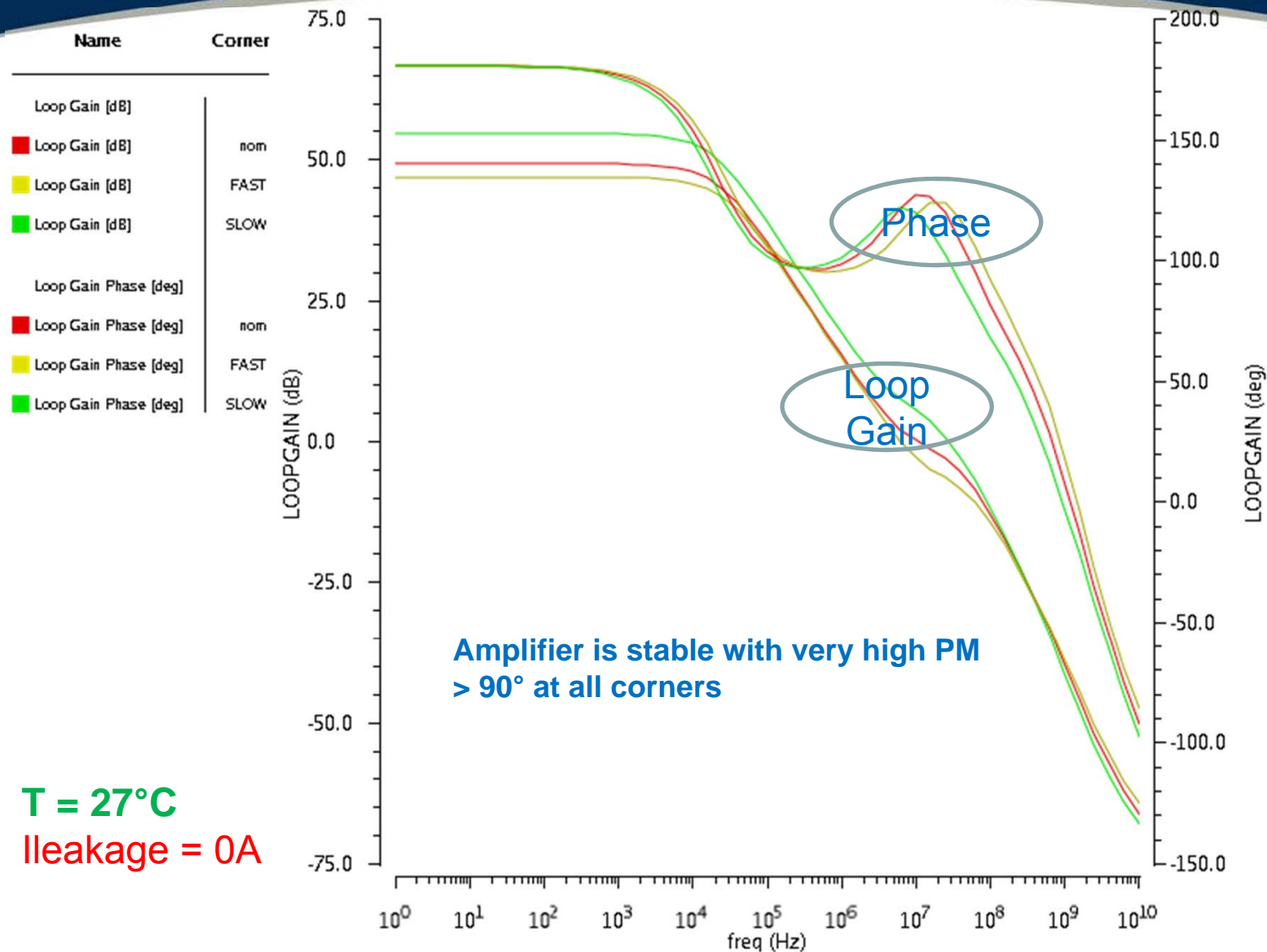


Pre-amplifier open-loop gain



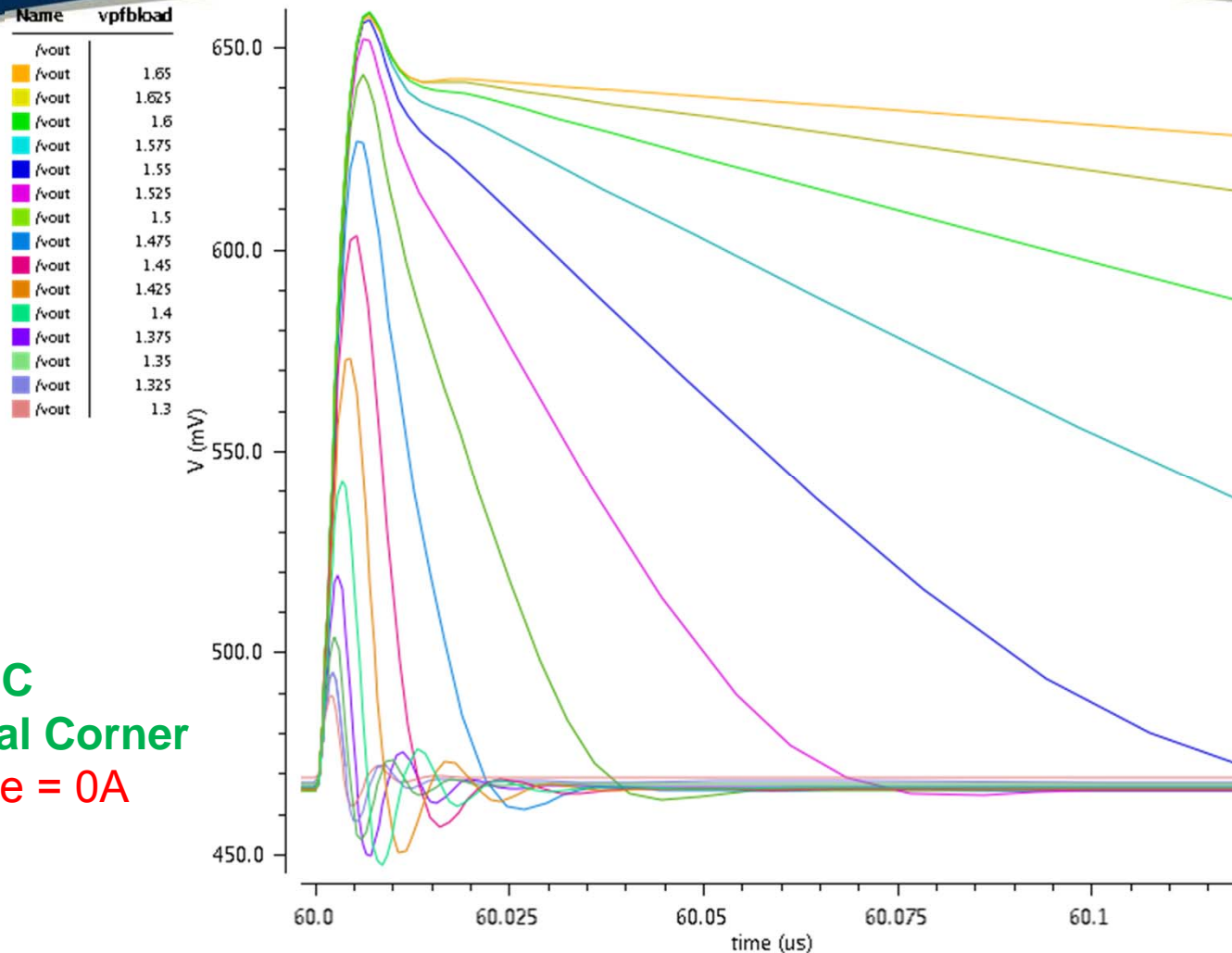


Pre-amplifier stability analysis at all corners





Pre-amp discharge control of pre-amplifier (2Ke-)



T = 27°C
Nominal Corner
Ileakage = 0A

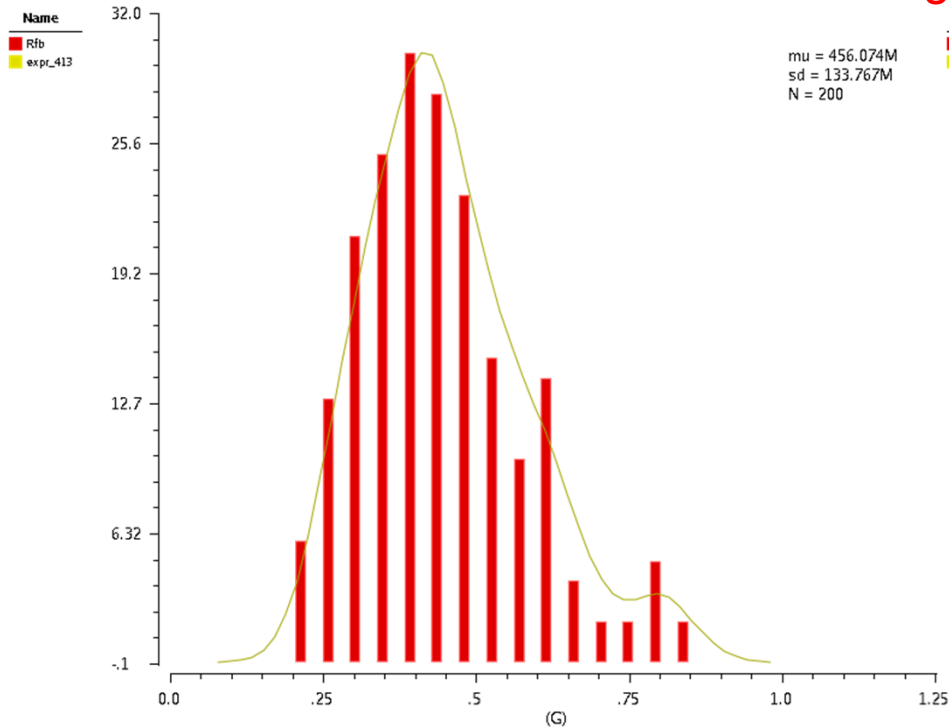
- Changing vPFBPreAmp from 1.3V to 1.65V in steps of 25mV
- Oscillations at high feedback current i.e. for vPFBPreAmp < 1.45V (expected)



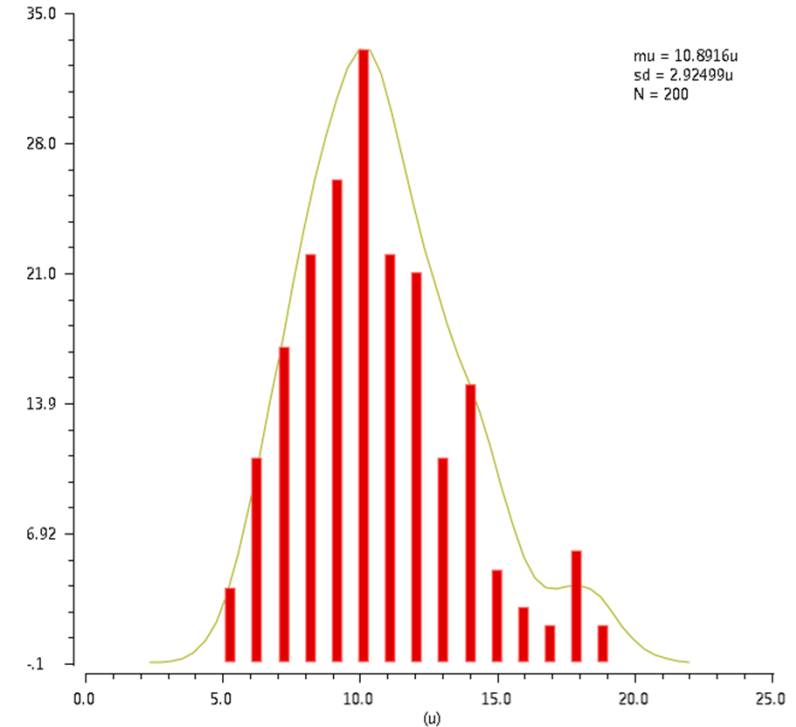
Pre-amp feedback resistance & recovery time variation (5Ke-)

T = - 40°C

Ileakage = 0A



Variation of feedback resistance



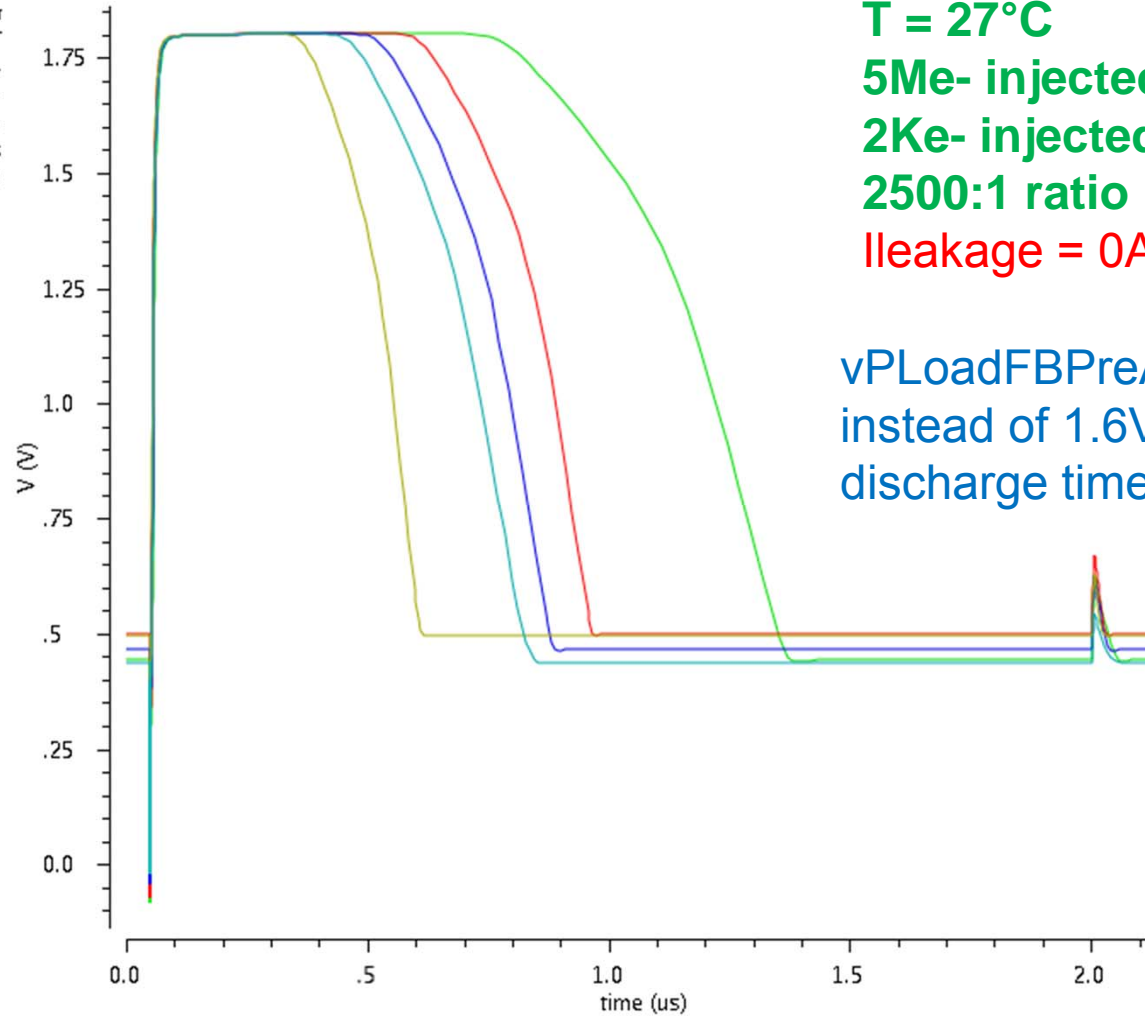
Variation of recovery time

200 MC iterations with vPLoadFBPreAmp set to 1.6V. The results show the variation of the pre-amplifier feedback resistance which affects the discharge time constant and as a result the recovery/discharge time



Overload Recovery of pre-amplifier @5Million e-

Name	Corner
f/vout	SF
f/vout	FAST
f/vout	SLOW
f/vout	FS
f/vout	NOM



T = 27°C

5Me- injected at 50ns

2Ke- injected at 2μs

2500:1 ratio

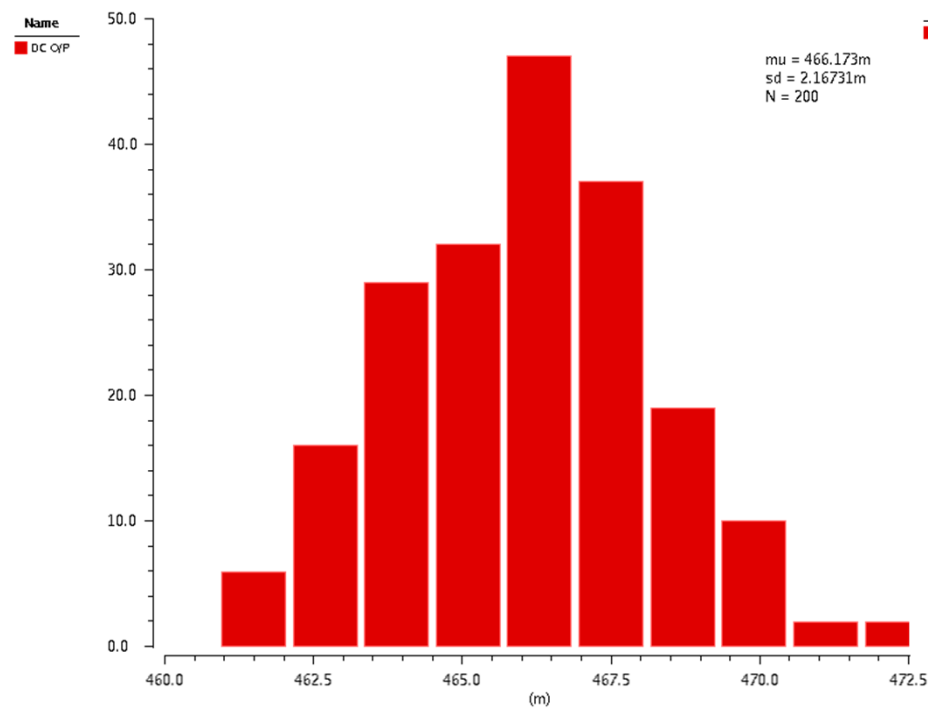
Ileakage = 0A

vPLoadFBPreAmp = 1.5V
instead of 1.6V to reduce
discharge time constant

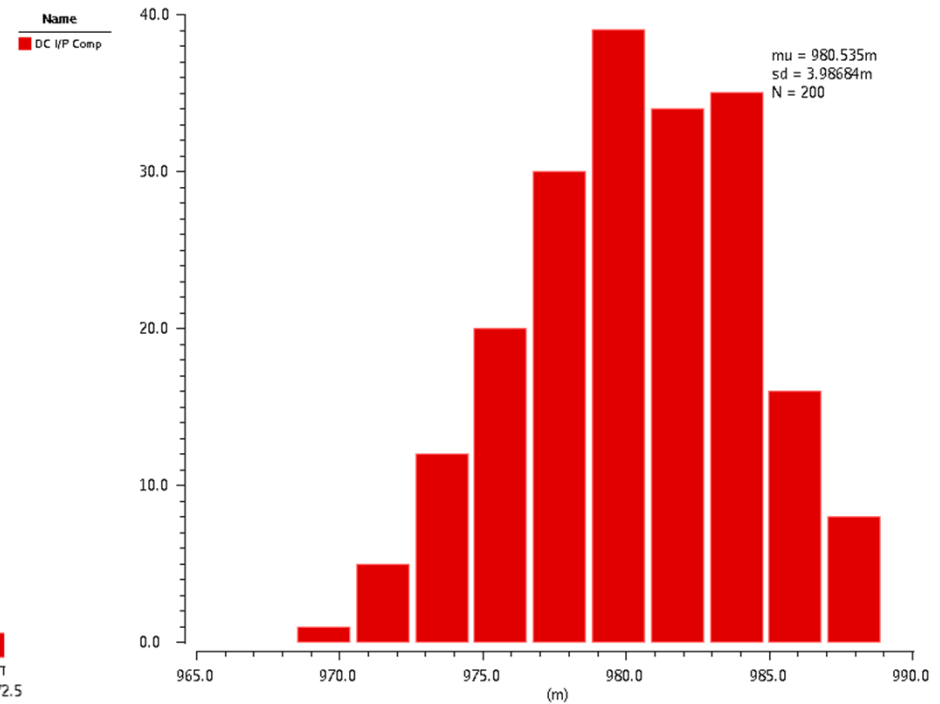
Return to base line within 2μs across all corners



Distribution of output DC level of pre-amplifier (Output DC level as Noise)



Before SF



After SF at comparator input

T = 27°C

Ileakage = 0A